Transistor Panasonic

2SB0766, 2SB0766A (2SB766, 2SB766A)

Silicon PNP epitaxial planar type

For low-frequency output amplification
Complementary to 2SD0874 (2SD874) and 2SD0874A (2SD874A)

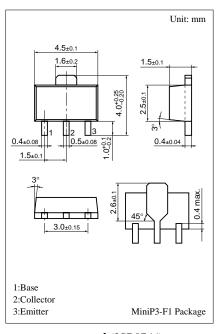
Features

- Large collector power dissipation P_C.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit	
Collector to	2SB0766	V	-30	v	
base voltage	2SB0766A	V_{CBO}	-60		
Collector to	2SB0766	17	-25	V	
emitter voltage	2SB0766A	V_{CEO}	-50		
Emitter to base voltage		V_{EBO}	-5	V	
Peak collector current		I_{CP}	-1.5	A	
Collector current		I_C	-1	A	
Collector power dissipation		${P_C}^*$	1	W	
Junction temperature		T _j	150	°C	
Storage temperature		T_{stg}	−55 ~ +150	°C	

^{*} Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion



Marking symbol : A(2SB0766) B(2SB0766A)

Electrical Characteristics (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I_{CBO}	$V_{CB} = -20V, I_E = 0$			- 0.1	μΑ
Collector to base	2SB0766		$I_{\rm C} = -10\mu{\rm A}, I_{\rm E} = 0$	-30			V
voltage	2SB0766A	V_{CBO}		-60			
Collector to emitter	2SB0766	**	$I_{\rm C} = -2mA, I_{\rm B} = 0$	-25			v
voltage	2SB0766A	V_{CEO}		-50			
Emitter to base voltage		V _{EBO}	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$	-5			V
Forward current transfer ratio		h _{FE1} *1	$V_{CE} = -10V, I_{C} = -500 \text{mA}^{*2}$	85		340	
		h _{FE2}	$V_{CE} = -5V, I_C = -1A^{*2}$	50			
Collector to emitter saturation voltage $V_{CE(sat)}$		V _{CE(sat)}	$I_C = -500 \text{mA}, I_B = -50 \text{mA}^{*2}$		- 0.2	- 0.4	V
Base to emitter saturation voltage $V_{BE(sat)}$		V _{BE(sat)}	$I_C = -500 \text{mA}, I_B = -50 \text{mA}^{*2}$		- 0.85	-1.2	V
Transition frequency f _T		f_{T}	$V_{CB} = -10V$, $I_E = 50$ mA, $f = 200$ MHz		200		MHz
Collector output capacitance C _o		C _{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	30	pF

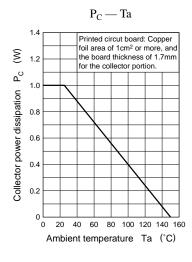
^{*1}hFE1 Rank classification

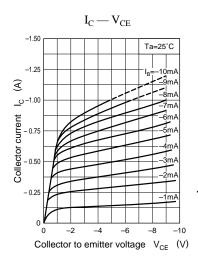
*2 Pulse measurement

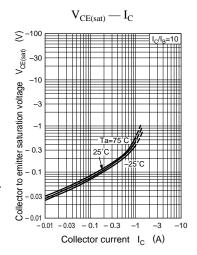
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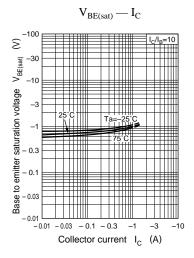
Note.) The Part numbers in the Parenthesis show conventional part number.

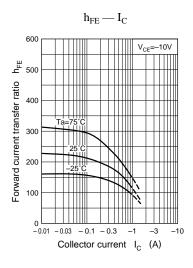
Rank Q R S 85 ~ 170 $120 \sim 240$ 170 ~ 340 h_{FE1} 2SB0766 AO AR AS Marking Symbol 2SB0766A BQ BR BS

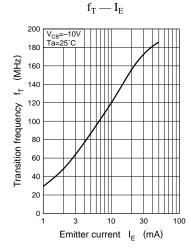


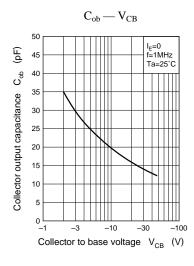


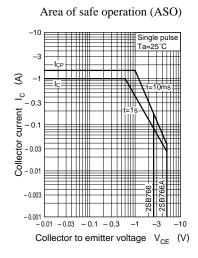












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